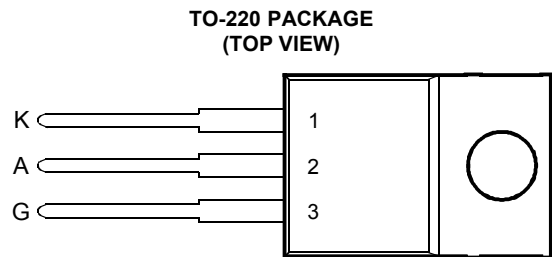


TIC116 SERIES SILICON CONTROLLED RECTIFIERS

- 8 A Continuous On-State Current
- 80 A Surge-Current
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 20 mA



Pin 2 is in electrical contact with the mounting base.

MDC1ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage	TIC116D	V_{DRM}	400	V
	TIC116M		600	
	TIC116S		700	
	TIC116N		800	
Repetitive peak reverse voltage	TIC116D	V_{RRM}	400	V
	TIC116M		600	
	TIC116S		700	
	TIC116N		800	
Continuous on-state current at (or below) 70°C case temperature (see Note 1)		$I_{T(RMS)}$	8	A
Average on-state current (180° conduction angle) at (or below) 70°C case temperature (see Note 2)		$I_{T(AV)}$	5	A
Surge on-state current at (or below) 25°C case temperature (see Note 3)		I_{TM}	80	A
Peak positive gate current (pulse width $\leq 300 \mu s$)		I_{GM}	3	A
Peak gate power dissipation (pulse width $\leq 300 \mu s$)		P_{GM}	5	W
Average gate power dissipation (see Note 4)		$P_{G(AV)}$	1	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply for continuous dc operation with resistive load. Above 70°C derate linearly to zero at 110°C.
 2. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 70°C derate linearly to zero at 110°C.
 3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
 4. This value applies for a maximum averaging time of 20 ms.

TIC116 SERIES

SILICON CONTROLLED RECTIFIERS

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM}	Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$T_C = 110^\circ\text{C}$			2	mA	
I_{RRM}	Repetitive peak reverse current	$V_R = \text{rated } V_{RRM}$	$I_G = 0$	$T_C = 110^\circ\text{C}$		2	mA	
I_{GT}	Gate trigger current	$V_{AA} = 12\text{ V}$	$R_L = 100\ \Omega$	$t_{p(g)} \geq 20\ \mu\text{s}$		8	20	mA
V_{GT}	Gate trigger voltage	$V_{AA} = 12\text{ V}$	$R_L = 100\ \Omega$	$T_C = -40^\circ\text{C}$			2.5	V
		$V_{AA} = 12\text{ V}$	$R_L = 100\ \Omega$			0.8	1.5	
		$V_{AA} = 12\text{ V}$	$R_L = 100\ \Omega$	$T_C = 110^\circ\text{C}$	0.2			
I_H	Holding current	$V_{AA} = 12\text{ V}$	Initiating $I_T = 100\text{ mA}$	$T_C = -40^\circ\text{C}$			100	mA
		$V_{AA} = 12\text{ V}$	Initiating $I_T = 100\text{ mA}$				40	
V_T	On-state voltage	$I_T = 8\text{ A}$	(see Note 5)			1.7	V	
dv/dt	Critical rate of rise of off-state voltage	$V_D = \text{rated } V_D$	$I_G = 0$	$T_C = 110^\circ\text{C}$		400		V/ μs

NOTE 5: This parameter must be measured using pulse techniques, $t_p = 300\ \mu\text{s}$, duty cycle $\leq 2\%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			3	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$